

# Chapt8Fig14a.m

## Total Elastic Ionized Impurity Scattering Rate

### Thomas-Fermi Screening with Angular Integration

Semiconductor Physics Documentation

#### Abstract

This document provides complete theoretical background and code analysis for Chapt8Fig14a.m, which calculates the total elastic scattering rate due to ionized impurities as a function of electron energy. The code employs Thomas-Fermi screening and numerical angular integration using the trapezoidal rule.

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# 1 Theoretical Foundation

## 1.1 Ionized Impurity Scattering Theory

**Axiom 1** (Fermi's Golden Rule for Scattering). *The scattering rate from state  $\mathbf{k}$  to state  $\mathbf{k}'$  is:*

$$W_{\mathbf{k} \rightarrow \mathbf{k}'} = \frac{2\pi}{\hbar} |V_{\mathbf{k}\mathbf{k}'}|^2 \delta(E_{\mathbf{k}'} - E_{\mathbf{k}}) \quad (1)$$

**Definition 1** (Screened Coulomb Matrix Element). *For ionized impurity scattering with Thomas-Fermi screening:*

$$V_{\mathbf{k}\mathbf{k}'} = \frac{e^2}{\varepsilon_0 \varepsilon_r} \cdot \frac{1}{q^2 + q_{TF}^2} \quad (2)$$

where  $q = |\mathbf{k}' - \mathbf{k}|$  is the momentum transfer.

## 1.2 Total Scattering Rate

**Theorem 1** (Total Elastic Scattering Rate). *The total scattering rate is obtained by integrating over all final states:*

$$\frac{1}{\tau(E)} = \sum_{\mathbf{k}'} W_{\mathbf{k} \rightarrow \mathbf{k}'} = n_i \int |V(q)|^2 g(\mathbf{k}') \delta(E' - E) d^3 k' \quad (3)$$

where  $n_i$  is the impurity concentration.

**Theorem 2** (Angular Integration Form). *For elastic scattering on a spherical Fermi surface:*

$$\frac{1}{\tau(E)} = \frac{\pi n_i m^*}{\hbar^3 k^3} \left( \frac{e^2}{4\pi \varepsilon_0 \varepsilon_r} \right)^2 \int_0^\pi \frac{\sin \theta}{(q^2 + q_{TF}^2)^2} d\theta \quad (4)$$

where  $q = 2k \sin(\theta/2)$ .

## 1.3 Change of Variables

**Lemma 1** (Substitution to  $\eta$ ). *With  $\eta = \sin(\theta/2)$ :*

- $q = 2k\eta$
- $d\eta = \frac{1}{2} \cos(\theta/2) d\theta$
- $\sin \theta = 2 \sin(\theta/2) \cos(\theta/2) = 2\eta \sqrt{1 - \eta^2}$

The integral becomes:

$$\int_0^\pi \frac{\sin \theta}{(q^2 + q_{TF}^2)^2} d\theta = \int_0^1 \frac{4\eta \sqrt{1 - \eta^2}}{(4k^2 \eta^2 + q_{TF}^2)^2} \cdot \frac{2d\eta}{\sqrt{1 - \eta^2}} \quad (5)$$

## 1.4 Thomas-Fermi Screening

**Definition 2** (Thomas-Fermi Wavevector).

$$q_{TF}^2 = \frac{k_F m^* e^2}{\pi^2 \hbar^2 \varepsilon_0 \varepsilon_r} \quad (6)$$

where  $k_F = (3\pi^2 n)^{1/3}$  is the Fermi wavevector.

## 2 Numerical Method: Trapezoidal Integration

### 2.1 The Trapezoidal Rule

**Theorem 3** (Trapezoidal Rule). *For a function  $f(x)$  on interval  $[a, b]$  with  $N$  subintervals of width  $h = (b - a)/N$ :*

$$\int_a^b f(x) dx \approx h \left[ \frac{f(a) + f(b)}{2} + \sum_{i=1}^{N-1} f(a + ih) \right] \quad (7)$$

**Theorem 4** (Error Estimate). *The error in the trapezoidal rule is:*

$$E_T = -\frac{(b-a)^3}{12N^2} f''(\xi) \quad (8)$$

for some  $\xi \in [a, b]$ . The method is second-order accurate:  $E_T = O(h^2)$ .

### 2.2 Application to Angular Integration

The code uses a simplified form where the step size equals the increment:

$$\int_0^\pi f(\theta) d\theta \approx \sum_{j=1}^{180} f(\theta_j) \cdot \Delta\theta \quad (9)$$

where  $\Delta\theta = \pi/180$  radians ( $1^\circ$  steps).

## 3 Line-by-Line Code Analysis

### 3.1 Function Declaration

```
1 function TFelasticScattering
2 clear; clf;
```

Declares as a function and clears workspace.

### 3.2 Physical Constants

```
1 m0=9.109382e-31;
2 echarge=1.6021764e-19;
3 hbar=1.05457159e-34;
4 epsilon0=8.8541878e-12;
```

$$m_0, e, \hbar, \epsilon_0 \quad (10)$$

Fundamental physical constants in SI units.

```
1 ezero=13.2;
2 m1=0.070;
```

$$\epsilon_r = 13.2, \quad m^* = 0.07m_0 \quad (11)$$

GaAs material parameters.

```
1 emax=300.0d-3;
2 n=1.0d16;
3 npoints = 200;
```

$$E_{\max} = 300 \text{ meV}, \quad n_{\text{initial}} = 10^{16} \text{ cm}^{-3} \quad (12)$$

Maximum energy for plot and starting carrier density.

### 3.3 Carrier Density Loop

```

1   for k=1:2
2     n=n*10;

```

$$n \in \{10^{17}, 10^{18}\} \text{ cm}^{-3} \quad (13)$$

*Loop over two carrier densities (plotted as two curves).*

```

1   kF1=(3*(pi^2)*n)^(1/3);
2   kF1=kF1*1.e2;

```

$$k_F = (3\pi^2 n)^{1/3} \times 10^2 \text{ (convert cm}^{-1} \rightarrow \text{m}^{-1}) \quad (14)$$

*Fermi wavevector calculation and unit conversion.*

```

1   kF2=kF1^2;
2   kF3=kF1^3;

```

$$k_F^2, k_F^3 \quad (15)$$

*Powers of Fermi wavevector for later use.*

### 3.4 Thomas-Fermi Screening Wavevector

```

1   qTF2=kF1*m0*m1*(echarge^2)/(epsilon0*ezero*(pi^2)*(hbar^2));

```

$$q_{TF}^2 = \frac{k_F m_0 m_1 e^2}{\epsilon_0 \epsilon_r \pi^2 \hbar^2} \quad (16)$$

*Thomas-Fermi wavevector squared.*

### 3.5 Fermi Energy

```

1   eF=((hbar*kF1)^2)/(2.0*m0*m1*echarge);

```

$$E_F = \frac{(\hbar k_F)^2}{2m^*} \cdot \frac{1}{e} \text{ [eV]} \quad (17)$$

*Fermi energy in eV (division by e converts from J to eV).*

### 3.6 Constant Prefactor

```

1   const=(pi*n*1.0e6*(echarge^4)*m0*m1);
2   const=const/(((4.*pi*epsilon0)^2)*(ezero^2)*(hbar^3));

```

$$C = \frac{\pi n \cdot 10^6 \cdot e^4 \cdot m_0 m_1}{(4\pi\epsilon_0)^2 \epsilon_r^2 \hbar^3} \quad (18)$$

*Prefactor for scattering rate (includes unit conversion).*

### 3.7 Energy Grid Setup

```

1   emin=eF;
2   demax=(emax-emin)/200.0;
3   dth=pi/180.0;

```

$$E_{\min} = E_F, \quad \Delta E = \frac{E_{\max} - E_F}{200}, \quad \Delta\theta = \frac{\pi}{180} \quad (19)$$

*Energy step and angular step (1° increments).*

### 3.8 Main Energy Loop

```

1 ei=emin;
2 for i=1:npoints
3   ei=ei+demax;
4   ak=(sqrt(2.*m0*m1*ei*echarge))/hbar;
5   ak3=ak^3;

```

$$k = \frac{\sqrt{2m^*E \cdot e}}{\hbar}, \quad k^3 \quad (20)$$

*Electron wavevector at each energy.*

### 3.9 Angular Integration Loop

```

1 aint1=0.0;
2 theta=0.0;
3 for j=1:180
4   theta=theta+dth;
5   aint1=aint1+(dth*gchi1(theta,ak,qTF2));
6 end

```

$$I = \sum_{j=1}^{180} g(\theta_j) \cdot \Delta\theta \quad (21)$$

*Trapezoidal integration over angle (calls helper function gchi1).*

### 3.10 Store Results

```

1 y1(i)=const*aint1/ak3;
2 x1(i)=ei*1.d3;

```

$$\frac{1}{\tau(E)} = \frac{C \cdot I}{k^3}, \quad E \text{ [meV]} \quad (22)$$

*Scattering rate calculation and energy in meV.*

### 3.11 Helper Function: gchi1

```

1 function gchi1 = gchi1(theta,k,qTF2)
2 x=2.0*k*sin(theta/2.0);
3 x2=x^2;
4 g=(tan(theta/2.0))*((sin(theta/2.))^2)*((1.0+(qTF2/x2))^2);
5 gchi1=1.0/g;
6 return

```

$$g(\theta) = \frac{1}{\tan(\theta/2) \cdot \sin^2(\theta/2) \cdot (1 + q_{\text{TF}}^2/q^2)^2} \quad (23)$$

where  $q = 2k \sin(\theta/2)$ .

*This computes the integrand for the angular integration.*

### 3.12 Plotting

```

1 figure(1); hold on; plot(x1,y1,'r'); axis([0,emax*1.d3,0,16e12]);

```

*Plot scattering rate vs energy with axis limits.*

## 4 Physical Interpretation

### 4.1 Energy Dependence

The scattering rate  $1/\tau(E)$  typically:

- Decreases with increasing energy (faster electrons harder to scatter)
- Scales approximately as  $E^{-3/2}$  at high energy
- Has a plateau or peak near  $E_F$

### 4.2 Density Dependence

Higher carrier density leads to:

- Stronger screening (larger  $q_{TF}$ )
- Lower scattering rate at small angles
- But higher overall scattering due to more impurities (if  $n_i = n$ )

## 5 Summary

This code calculates the total elastic scattering rate by numerically integrating over all scattering angles using the trapezoidal rule. The helper function `gchi1` encodes the screened Coulomb scattering matrix element with Thomas-Fermi screening. Results show how scattering rate varies with electron energy and carrier density.